

ABSTRACT

A method for forming structures self-aligned with each other on a semiconductor substrate, comprising the following steps: Forming, on the semiconductor substrate, first regions of a first material projecting from the semiconductor substrate; forming, over the whole of the semiconductor substrate, a protective layer of a second material selective with respect to the first material; removing the protective layer to expose said first regions through a planarizing step; etching said first regions to expose said semiconductor substrate, and forming second regions projecting from the substrate of said protective layer. Advantageously, spacers are formed on the sidewalls of the first regions.